NSN 5961-00-402-8161

Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-402-8161 **Inclosure Material:** Glass and metal **Overall Length:** 0.404 inches Overall Diameter: Between 0.501 inches and 0.510 inches **Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Anode **Mounting Method: Terminal Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 480.0 nonrepetitive peak reverse voltage, peak total value and 400.0 repetitive peak reverse voltage, peak total value and 400.0 breakover voltage, dc and 2.0 gate trigger voltage, dc **Current Rating Per Characteristic:** 900.00 amperes forward current, peak total value and 35.00 amperes forward current, total rms and 10.00 milliamperes breakover current, dc and 80.00 milliamperes gate trigger current, dc and 70.00 milliamperes holding current, dc **Power Rating Per Characteristic:** 30.0 watts total device dissipation **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius ambient air **Special Features:** Junction pattern arrangement: pnpn **Test Data Document:** 50985-8879600001 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 2 solder stud and 1 case Shelf Life: N/a **Unit Of Measure: Demilitarization:**

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No